

1763

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Docket No.: 4425-211

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of

TSAI, TENG-CHUN

U.S. Patent Application No. 09/986,929

Filed: November 13, 2001

Group Art Unit: 1763

Examiner: George A. Goudreau

For: METHOD OF FORMING A DUAL DAMASCENE VIA BY USING A METAL HARD MASK LAYER

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OCT 28 2003
TC 1700

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

By Official Action mailed September 24, 2003, restriction to a single disclosed species from each group listed on page 2 of the Restriction Requirement is required.

In response, Applicants hereby elect:

Group I

- 1) second metal is Ti (i.e. claims 2, 11, 23)

Group II

- 1) middle etch stop is Si₃N₄ (i.e. claims 8, 17, 29)

Group III

- 1) barrier layer is TaN/Ta (i.e. claims 20, 32)

Group IV

- 1) hard mask is SiC (i.e. claim 34)

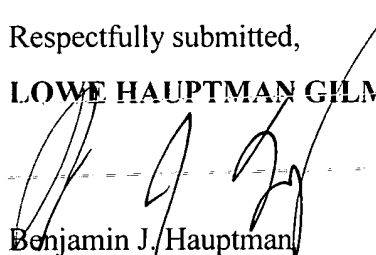
Claims 1, 10, 19, 22, and 31 are generic claims and should be examined with the above-listed elected claims.

Early examination on the merits is courteously solicited.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 07-1337 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: October 24, 2003